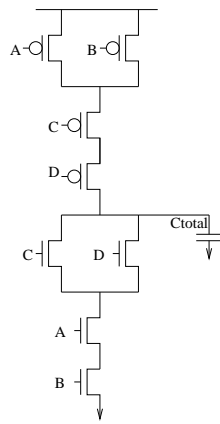
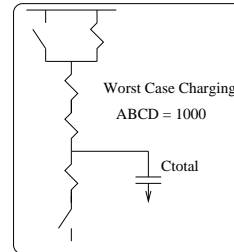
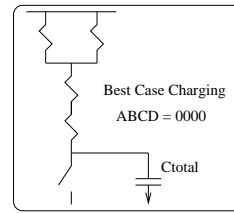


Modelling Complex CMOS gates

Replace each transistor with its equivalent resistance and simplify the resistor network down to one R_{eff} resistance.



WARNING
Reff is 'pattern dependent'



* Assumes all transistors are the same size.

As with the capacitances, it is useful to define a baseline R_{nmin} and R_{pmin}

R_{pmin} : Resistance of a minimum W/L PMOS in a technology

R_{nmin} : Resistance of a minimum W/L NMOS in a technology

Beware: These are MAXIMUM channel resistances.

Increasing the width beyond the minimum will lower resistance.

Example: For a given inverter, you know the total load $C_{total}=4fF$.

Detailed SPICE simulations reveal that $t_{phl} = 60ps$ and $t_{plh} = 118ps$.

The W/L ratio of the NMOS is $220nm/180nm$ and is minimum size.

The W/L ratio of the PMOS is $360nm/180nm$

Determine the R_{eff} of the PMOS and NMOS. Also determine R_{pmin} and R_{nmin}

$$t_{phl} = 0.69 R_{pms} C_{total}$$

$$R_{pms} = 118ps / 0.69 * 4f = 42.75k \text{ Ohm}$$

Minimum width is $220nm$

$$360/220 = R_{pmin}/42.75k$$

$$R_{pmin} = 69.95k$$

$$t_{plh} = 0.69 R_{nms} C_{total}$$

$$R_{nms} = 60ps / 0.69 * 4f = 21.74k \text{ Ohm}$$

Since this is already minimum sized,

$$R_{nmin} = 21.74k \text{ Ohm}$$

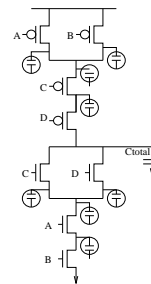
Things we are not taking into account

- 1) In complex gates there are all of the intermediate drain capacitances which may need to be charged and discharged.

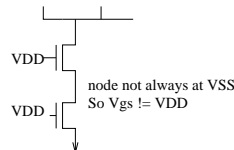
We do account for the C_d capacitances directly on the output node by including them in C_{total}

The others are hard to account for in most cases.

See Elmore's delay model for a good approximation.



- 2) The approximation that $D = 0.69 R_{eff} C_{total}$ assumes a step input. For slightly sloped inputs (t_r or $t_f < 1/2 D$) it is still a good approximation.
- 3) In gates other than an inverter, we don't have full $V_{gs} = V_{DD}$ or $-V_{DD}$



- 4) For the same reason as above, since the bulk to source voltage $\neq 0$, the effective threshold voltage (V_{th}) changes
- 5) We use first order model approximations to get R_{eff} . This does not account for the non-linearities.

Conclusion

Given an arbitrary CMOS circuit with arbitrary transistor sizes, you should be able to determine the simplified RC delay in terms of C_{gmin} , C_{dmin} , R_{pmin} , R_{nmin}

Given either technology constants or simulation results, you should be able to determine C_{gmin} , C_{dmin} , R_{pmin} and R_{nmin} .